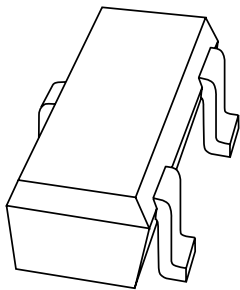


# DATA SHEET



**2PB709AW**

PNP general purpose transistor

Product data sheet

2002 Jun 26

PNP general purpose transistor

2PB709AW

FEATURES

- High collector current (max. 100 mA)
- Low collector-emitter saturation voltage (max. 500 mV).

APPLICATIONS

- General purpose switching and amplification.

DESCRIPTION

PNP transistor in an SC-70 (SOT323) plastic package.  
NPN complement: 2PD601AW

MARKING

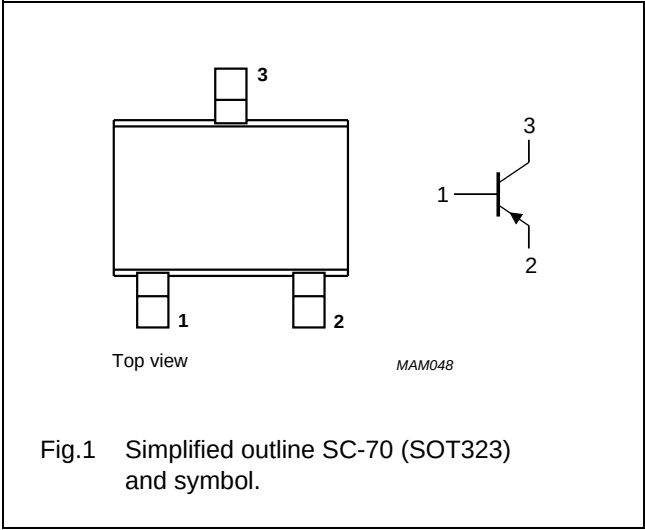
| TYPE NUMBER | MARKING CODE <sup>(1)</sup> |
|-------------|-----------------------------|
| 2PB709AQW   | N5*                         |
| 2PB709ARW   | N7*                         |
| 2PB709ASW   | N9*                         |

Note

1. \* = p: made in Hong Kong.  
\* = t: made in Malaysia.

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1   | base        |
| 2   | emitter     |
| 3   | collector   |



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL           | PARAMETER                     | CONDITIONS                       | MIN. | MAX. | UNIT |
|------------------|-------------------------------|----------------------------------|------|------|------|
| V <sub>CBO</sub> | collector-base voltage        | open emitter                     | –    | –45  | V    |
| V <sub>CEO</sub> | collector-emitter voltage     | open base                        | –    | –45  | V    |
| V <sub>EBO</sub> | emitter-base voltage          | open collector                   | –    | –6   | V    |
| I <sub>C</sub>   | collector current (DC)        |                                  | –    | –100 | mA   |
| I <sub>CM</sub>  | peak collector current        |                                  | –    | –200 | mA   |
| P <sub>tot</sub> | total power dissipation       | T <sub>amb</sub> ≤ 25 °C; note 1 | –    | 200  | mW   |
| T <sub>stg</sub> | storage temperature           |                                  | –65  | +150 | °C   |
| T <sub>j</sub>   | junction temperature          |                                  | –    | 150  | °C   |
| T <sub>amb</sub> | operating ambient temperature |                                  | –65  | +150 | °C   |

Note

1. For mounting conditions, see “Thermal considerations and footprint design for SOT323 in the General Part of Data Handbook SC18”.

## PNP general purpose transistor

2PB709AW

## THERMAL CHARACTERISTICS

| SYMBOL        | PARAMETER                                   | CONDITIONS | VALUE | UNIT |
|---------------|---------------------------------------------|------------|-------|------|
| $R_{th\ j-a}$ | thermal resistance from junction to ambient | note 1     | 625   | K/W  |

## Note

- For mounting conditions, see "Thermal considerations and footprint design for SOT323 in the General Part of Data Handbook SC18".

## CHARACTERISTICS

$T_{amb} = 25\text{ °C}$  unless otherwise specified.

| SYMBOL      | PARAMETER                            | CONDITIONS                                                            | MIN. | MAX. | UNIT          |
|-------------|--------------------------------------|-----------------------------------------------------------------------|------|------|---------------|
| $I_{CBO}$   | collector-base cut-off current       | $I_E = 0$ ; $V_{CB} = -45\text{ V}$                                   | –    | –10  | nA            |
|             |                                      | $I_E = 0$ ; $V_{CB} = -45\text{ V}$ ; $T_j = 150\text{ °C}$           | –    | –5   | $\mu\text{A}$ |
| $I_{EBO}$   | emitter-base cut-off current         | $I_C = 0$ ; $V_{EB} = -5\text{ V}$                                    | –    | –10  | nA            |
| $h_{FE}$    | DC current gain                      | $I_C = -2\text{ mA}$ ; $V_{CE} = -10\text{ V}$                        |      |      |               |
|             | 2PB709AQW                            |                                                                       | 160  | 260  |               |
|             | 2PB709ARW                            |                                                                       | 210  | 340  |               |
|             | 2PB709ASW                            |                                                                       | 290  | 460  |               |
| $V_{CEsat}$ | collector-emitter saturation voltage | $I_C = -100\text{ mA}$ ; $I_B = -10\text{ mA}$ ; note 1               | –    | –500 | mV            |
| $C_c$       | collector capacitance                | $I_E = I_E = 0$ ; $V_{CB} = -10\text{ V}$ ; $f = 1\text{ MHz}$        | –    | 5    | pF            |
| $f_T$       | transition frequency                 | $I_C = -1\text{ mA}$ ; $V_{CE} = -10\text{ V}$ ; $f = 100\text{ MHz}$ |      |      |               |
|             | 2PB709AQW                            |                                                                       | 60   | –    | MHz           |
|             | 2PB709ARW                            |                                                                       | 70   | –    | MHz           |
|             | 2PB709ASW                            |                                                                       | 80   | –    | MHz           |

## Note

- Pulse test:  $t_p \leq 300\text{ }\mu\text{s}$ ;  $\delta \leq 0.02$ .

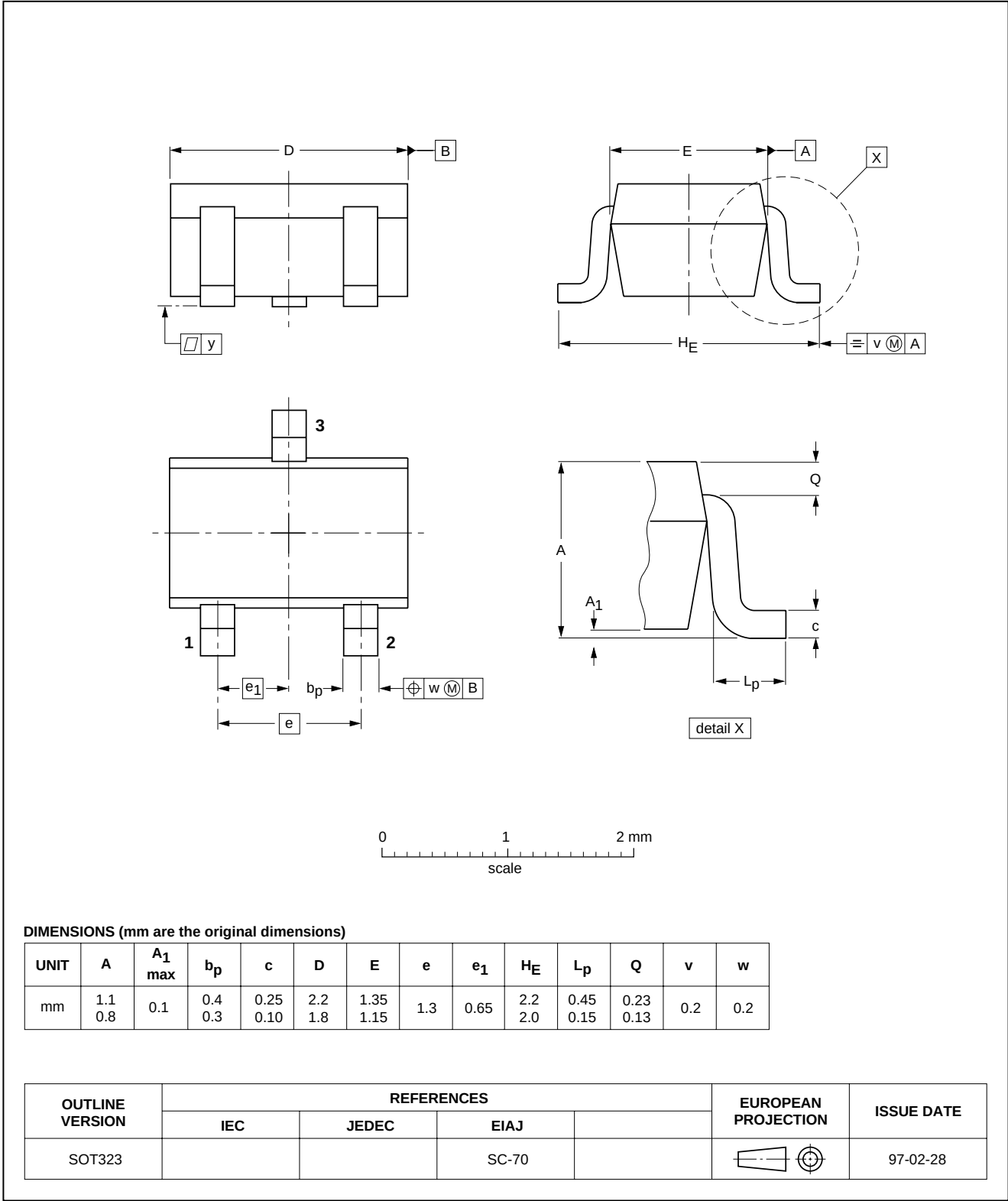
PNP general purpose transistor

2PB709AW

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



## PNP general purpose transistor

2PB709AW

## DATA SHEET STATUS

| DOCUMENT STATUS <sup>(1)</sup> | PRODUCT STATUS <sup>(2)</sup> | DEFINITION                                                                            |
|--------------------------------|-------------------------------|---------------------------------------------------------------------------------------|
| Objective data sheet           | Development                   | This document contains data from the objective specification for product development. |
| Preliminary data sheet         | Qualification                 | This document contains data from the preliminary specification.                       |
| Product data sheet             | Production                    | This document contains the product specification.                                     |

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